

2825

PTO/SB/21 (05-03) Approved for use through 04/30/2003. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE a collection of information unless it displays a valid OMB control number Reduction Act of 1995, no persons are required to respond to Application Number 09/955,810 TRANSMITTAL Filing Date September 19, 2001 **FORM** First Named Inventor Yoshiyuki Tanaka, et al. Art Unit 2825 (to be used for all correspondence after initial filing) **Examiner Name** Lee Calvin Attorney Docket Number 075834.00111 Total Number of Pages in This Submission **ENCLOSURES** (Check all that apply) After Allowance communication Fee Transmittal Form Drawing(s) to Group Appeal Communication to Board Licensing-related Papers Fee Attached of Appeals and Interferences Appeal Communication to Group (Appeal Notice, Brief, Reply Brief) Amendment/Reply Petition to Convert to a Proprietary Information Provisional Application After Final Power of Attorney, Revocation Status Letter Change of Correspondence Address Affidavits/declaration(s) Other Enclosure(s) (please Terminal Disclaimer Extension of Time Request Identify below): Post Card Request for Refund **Express Abandonment Request** CD, Number of CD(s) Information Disclosure Statement Remarks Certified Copy of Priority Document(s) The Commissioner is hereby authorized technarge any fees due or to credit any overpayment to Deposit Account Response to Missing Parts/ Incomplete Application No. 50-1794.

L uı	nder 37 CFR 1.52 or 1.53	13 AB	27	
	SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT		200	_
Firm or Individual name	Robert J. Depke, Holland & Knight LLC 131 South Dearbern Street, 30th Floor, Chicago, IL 60603	.R 280	نت	
Signature	- Ille Liton,	0		
Date	26/20/03			_
	CERTIFICATE OF TRANSMISSION/MAILING			_

I hereby certify that this correspondence is being facsimile transmitted to the USPTO or deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on

the date shown below.

Signature

Typed or printed name Robert J. Depke

Response to Missing Parts

Date

£/20/03

This collection of information is required by 37 CFR 16. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to 12 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.



THE UNITED STATES PATENT AND TRADEMARK OFFICE

Yoshiyuki Tanaka et al.

Atty. Docket No.

075834.00111

Serial No.:

Applicants:

09/ 955,810

Group Art Unit:

2825

Filed:

September 19, 2001

Examiner:

Lee Calvin

Invention:

"PRODUCTION METHOD OF SEMICONDUCTOR DEVICE"

Assistant Commissioner of Patents

SIR:

AMENDMENT B

ant Commissioner of Patents
Alexandria, VA 22313-1450

In response to the Office Action dated May 21, 2003, please amend the application as follows:

IN THE CLAIMS:

(Previously Amended) A method for producing a semiconductor device including formation of an interlayer insulating film having a fluorine-doped silicon oxide layer above a substrate, the method comprising the steps of:

forming said fluorine-doped silicon oxide layer in a process chamber; and

forming a silicon oxide layer on said fluorine-doped silicon oxide layer in a same process chamber subsequent to formation of said fluorine-doped silicon oxide layer, said silicon oxide layer being formed at a temperature at least 10% higher than a film forming temperature of said fluorine-doped silicon oxide layer; thereby

forming said interlayer insulating film comprising said fluorine-doped silicon oxide layer and said silicon oxide layer formed thereon.

2. (Original) The method for producing a semiconductor device according to claim 1, wherein

a film forming temperature of said silicon oxide layer is equal or less than 450 °C.